

30V N-Channel Enhancement Mode MOSFET

Description

The AP10H03DF-L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 10A$

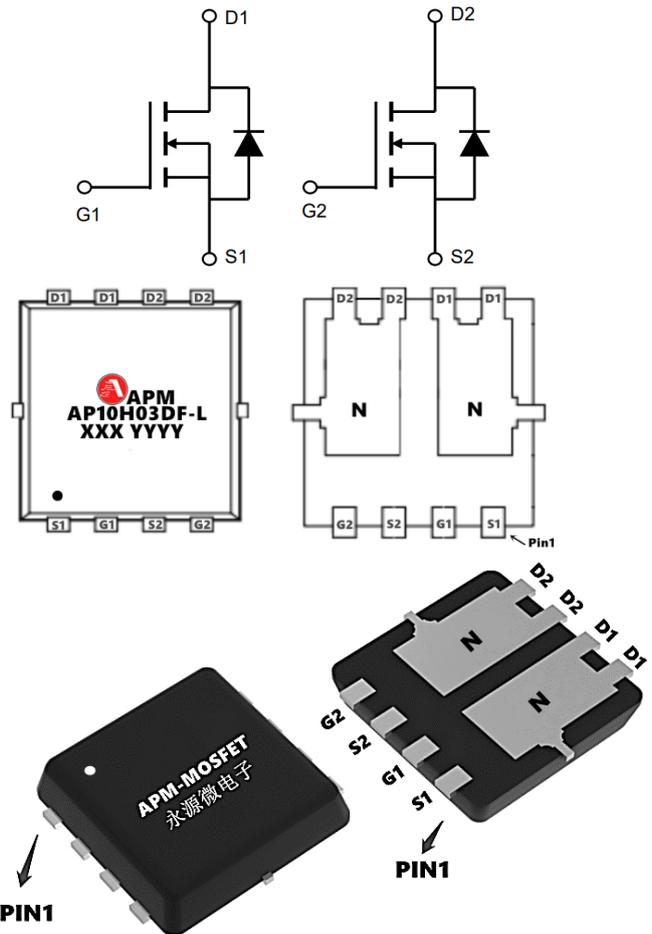
$R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=10V$ (Type: 13m Ω)

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP10H03DF-L	PDFN3*3-8L	AP10H03DF-L XXX YYYY	3000

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current	10	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current	8.9	A
I_{DM}	Pulsed Drain Current ²	57	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	85	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	$^\circ\text{C}/\text{W}$



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Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	32	---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.029	---	V/ $^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=5.8\text{A}$	---	12	18	m Ω
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=5\text{A}$	---	20	32	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-2.82	---	mV/ $^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=5\text{A}$	---	25	---	S
Rg	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.5	---	Ω
Qg	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=5.8\text{A}$	---	11.5	---	nC
Qgs	Gate-Source Charge		---	1.6	---	
Qgd	Gate-Drain Charge		---	2.9	---	
Td(on)	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3\Omega, I_D=5\text{A}$	---	5	---	ns
Tr	Rise Time		---	47.	---	
Td(off)	Turn-Off Delay Time		---	26	---	
Tf	Fall Time		---	8	---	
Ciss	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	860	---	pF
Coss	Output Capacitance		---	84	---	
Crss	Reverse Transfer Capacitance		---	70	---	
Is	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	5.8	A
VSD	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1\text{A}, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=12.7\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

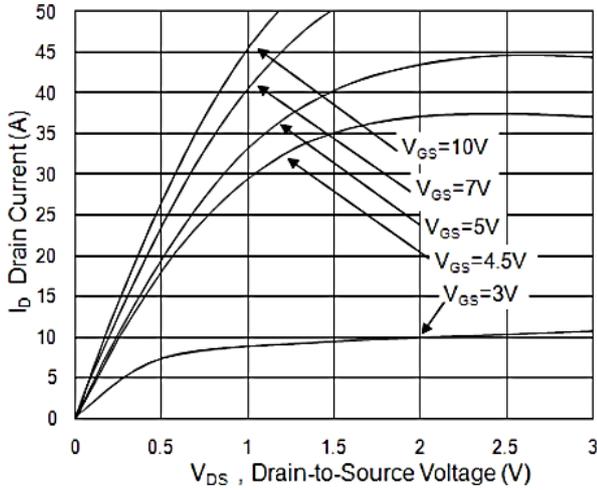


Fig.1 Typical Output Characteristics

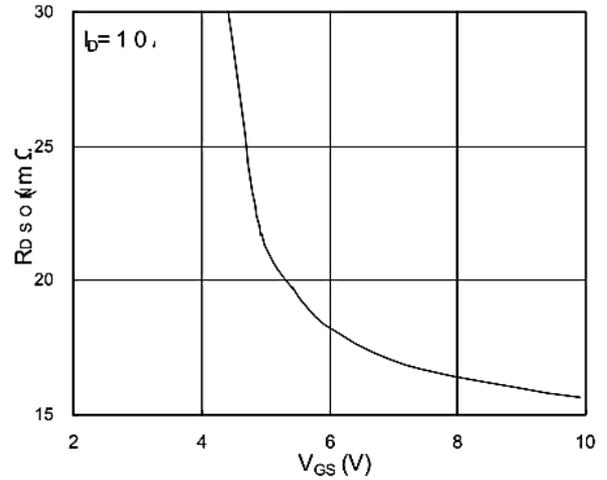


Fig.2 On-Resistance vs. Gate-Source

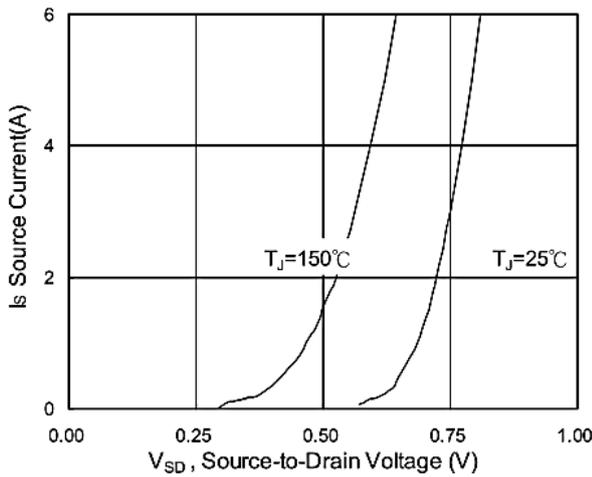


Fig.3 Forward Characteristics Of Reverse

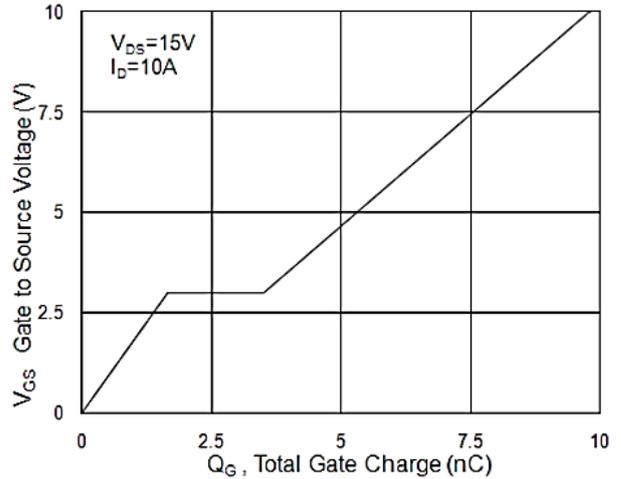


Fig.4 Gate-Charge Characteristics

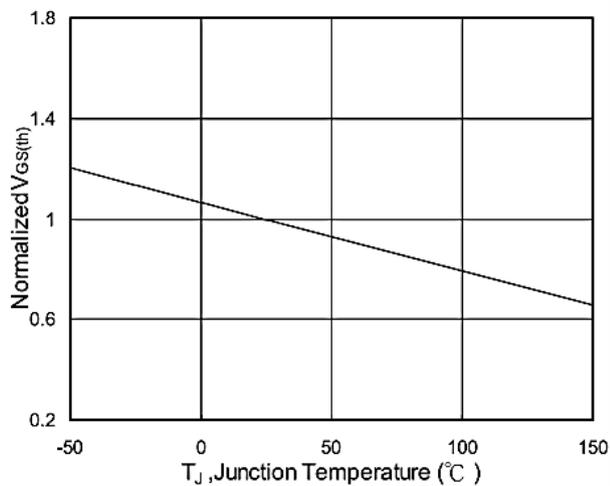


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

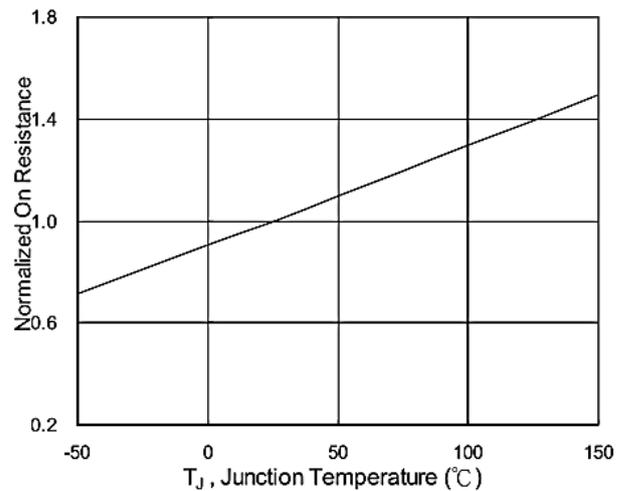


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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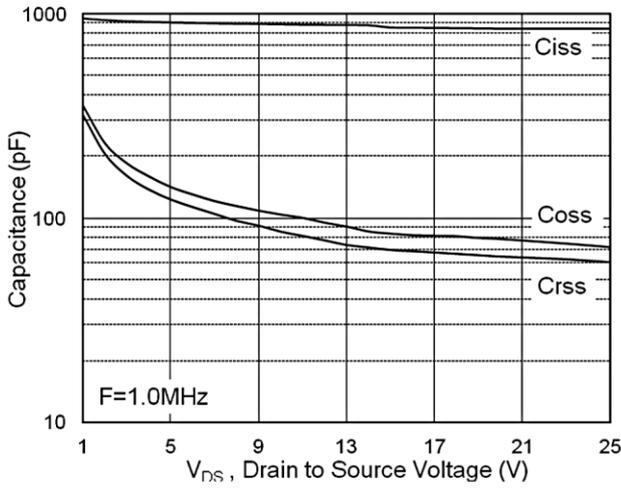


Fig.7 Capacitance

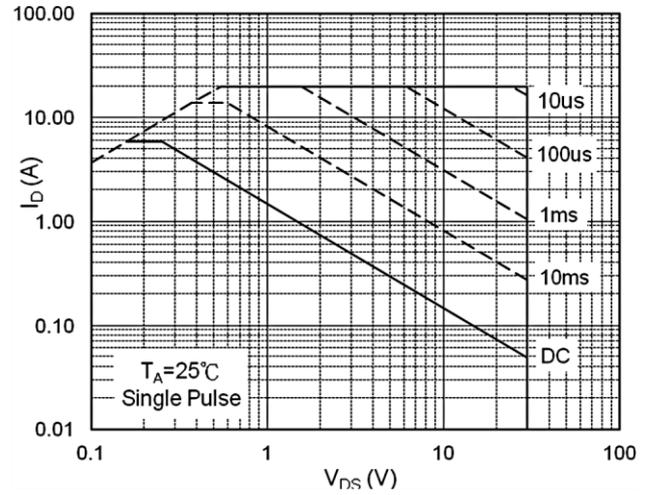


Fig.8 Safe Operating Area

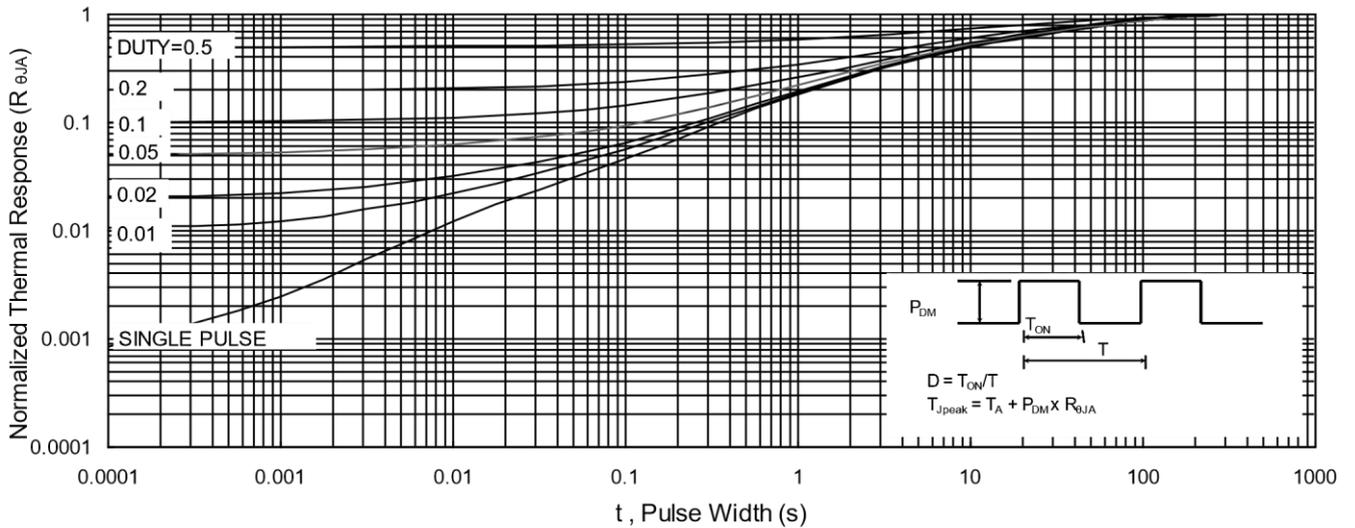


Fig.9 Normalized Maximum Transient Thermal Impedance

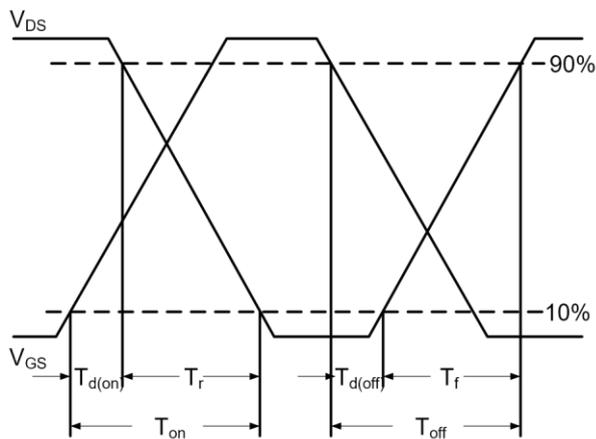


Fig.10 Switching Time Waveform

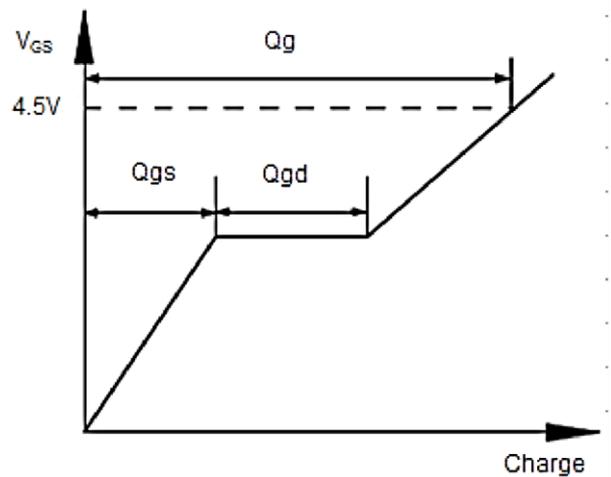
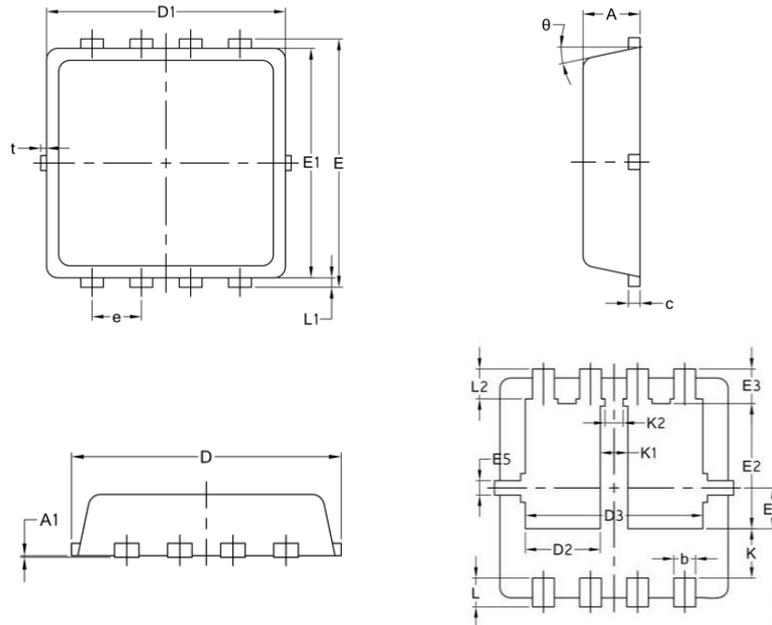


Fig.11 Gate Charge Waveform

Package Mechanical Data-PDFN3*3-8L Double



Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

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Edition	Date	Change
REV1.0	2024/1/31	Initial release

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